

### 2SC2881 TRANSISTOR (NPN)

#### FEATURES

Power dissipation

$$P_{CM}: 500 \text{ mW (Tamb=25}^\circ\text{C)}$$

Collector current

$$I_{CM}: 800 \text{ mA}$$

Collector-base voltage

$$V_{(BR)CBO}: 120 \text{ V}$$

Operating and storage junction temperature range

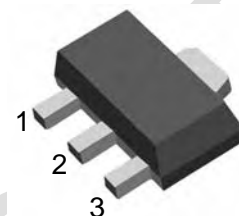
$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$

#### SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



#### ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=1\text{mA}, I_E=0$	120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	120			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=1\text{mA}, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=120\text{V}, I_E=0$			0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5\text{V}, I_C=0$			0.1	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE}=5\text{V}, I_C=100\text{mA}$	80		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{mA}, I_B=50\text{mA}$			1	V
Base-emitter voltage	$V_{BE}$	$V_{CE}=5\text{V}, I_C=500\text{mA}$			1	V
Transition frequency	$f_T$	$V_{CE}=5\text{V}, I_C=100\text{mA}$		120		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$			30	pF

#### CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	80-160	120-240
Marking	CO1	CY1